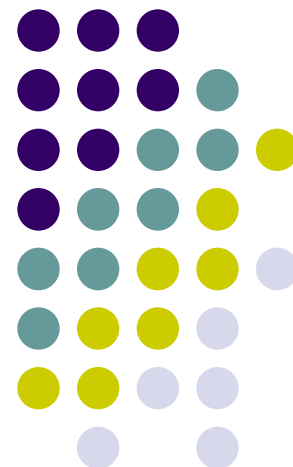


# VFCAL task status report

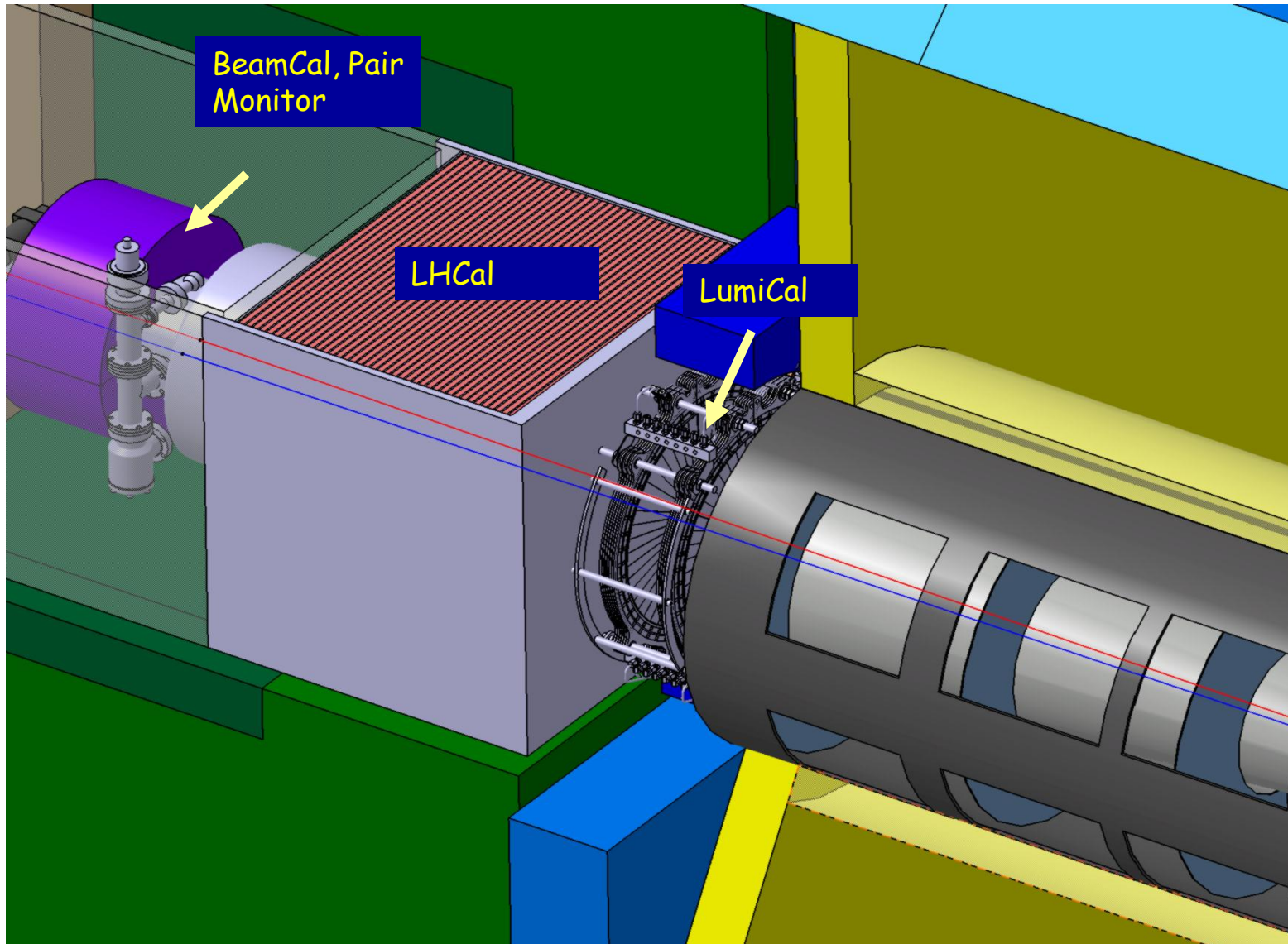
Sergej Schuwalow

DESY

On behalf of the FCAL collaboration



# Very Forward Region of the ILD Detector



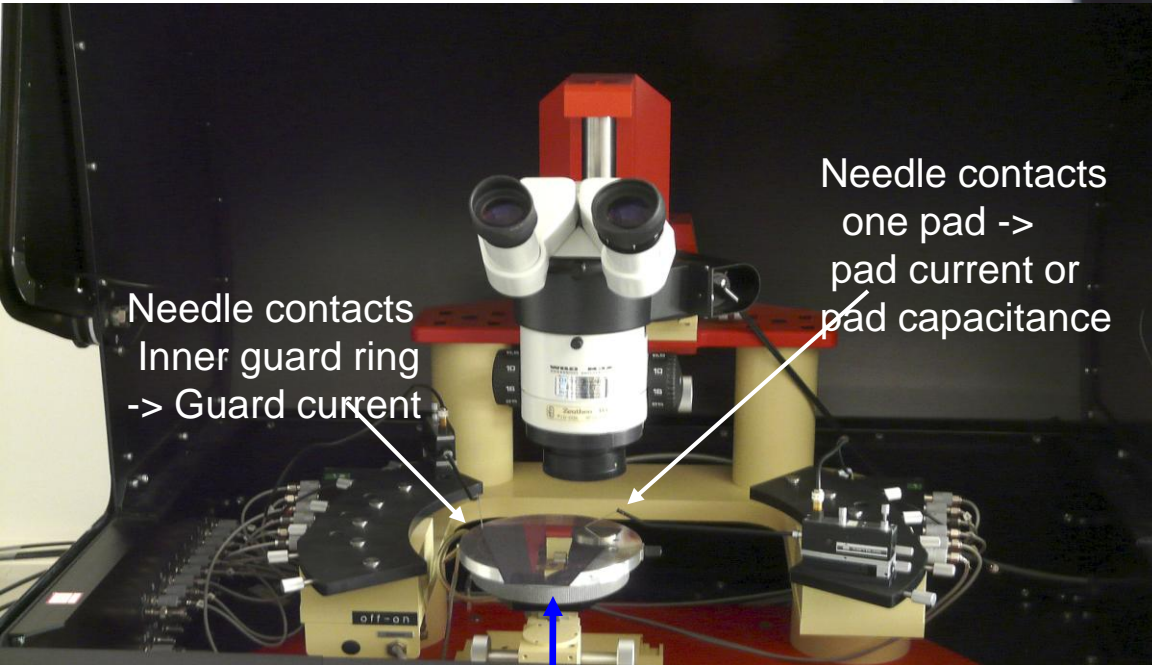
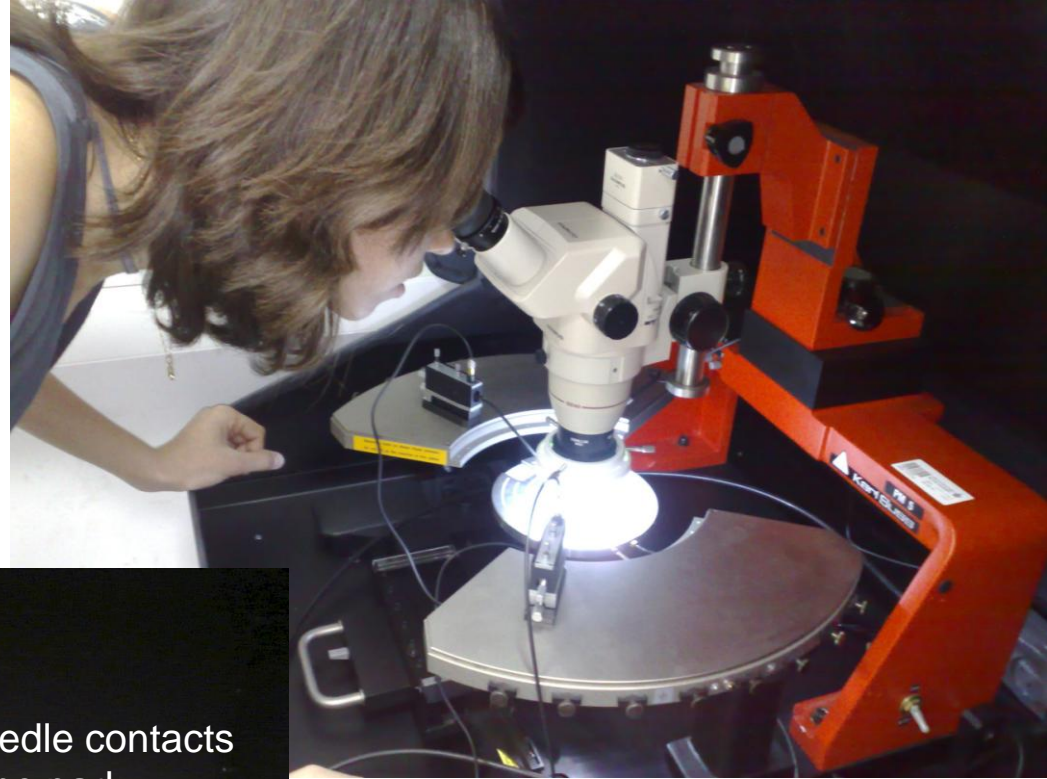
# Outline



- Infrastructure:
  - Probe stations, tests of LumiCal sensors
  - $^{90}\text{Sr}$  setup - sensor tests at the lab
  - high intensity beam measurements
- LumiCal sensor prototypes
- Laser Alignment System
- BeamCal sensor tests
- Readout electronics
- ADCs - recent developments **New!**
- System test at DESY testbeam, Aug 2010
- Future: full system test at the beam (FP7)

# Infrastructure: Probe Stations

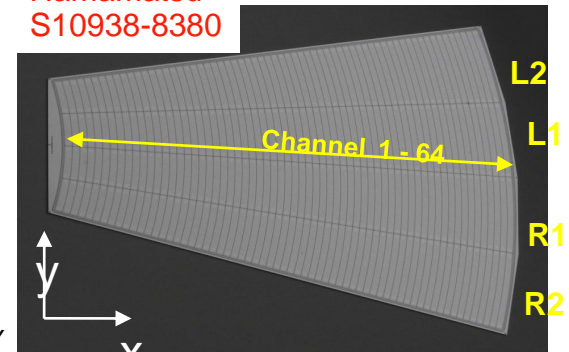
Tel-Aviv University



## DESY - Zeuthen

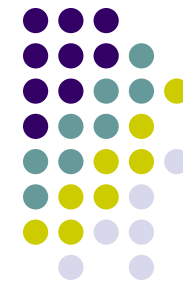
### LumiCal Sensor Tests

Hamamatsu  
S10938-8380

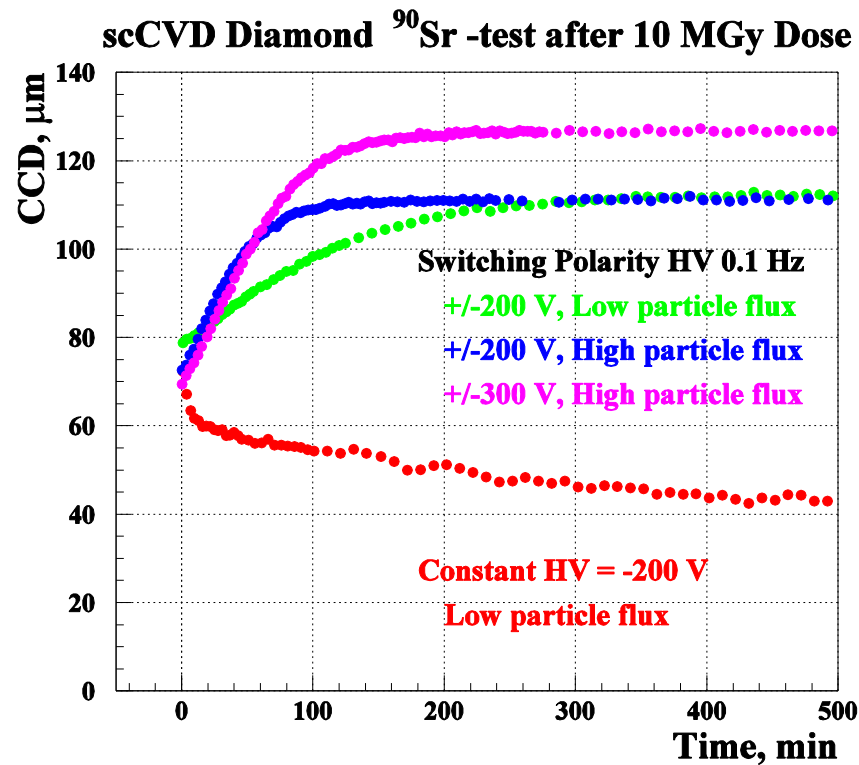
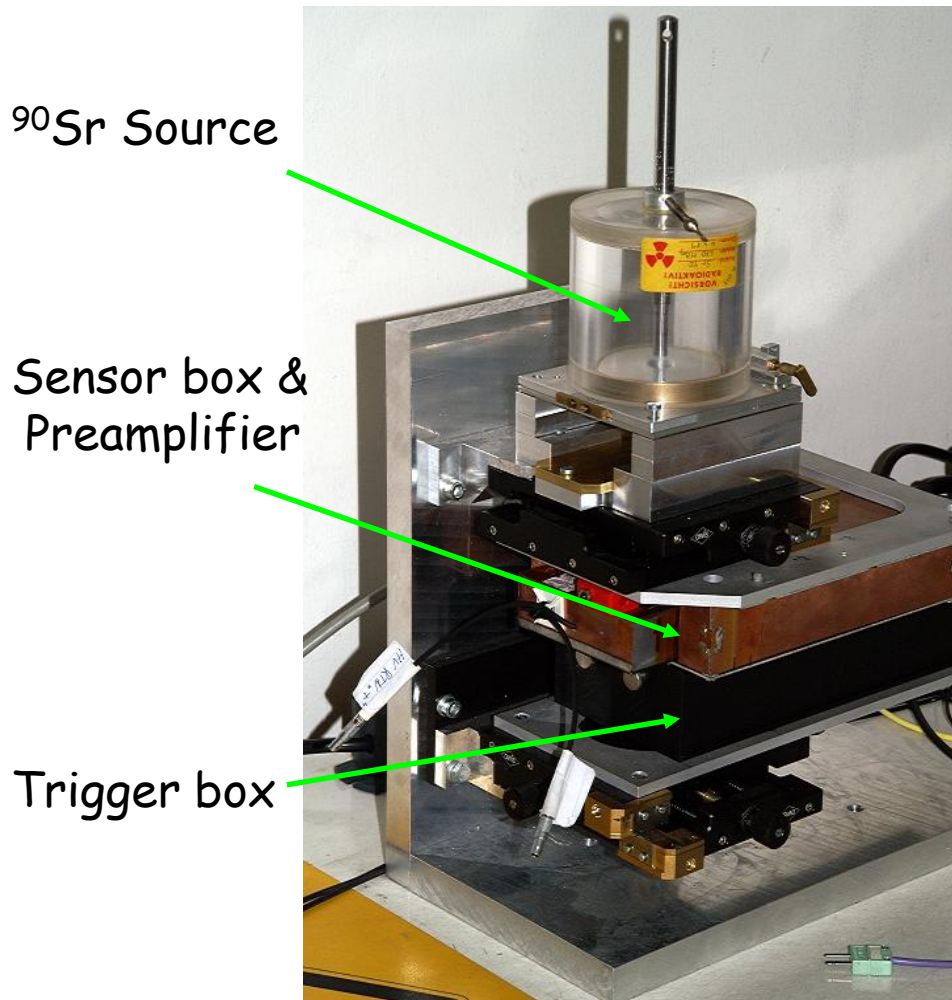


Backplane contacted via Al table ( '+' of high voltage)

# Infrastructure: BeamCal sensor tests in the lab

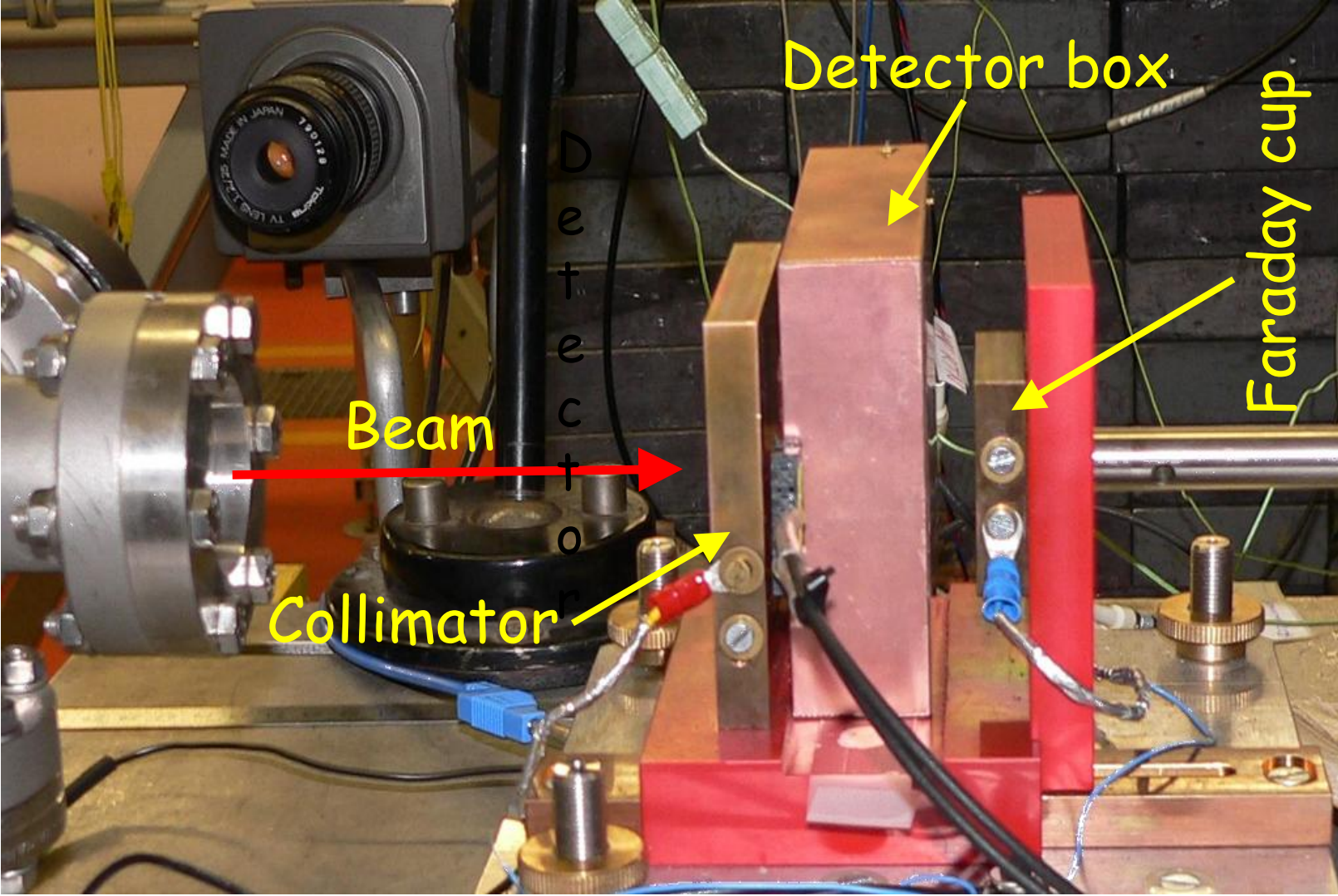


Detailed study of the rad. damaged sensors  
Influence of various operation conditions





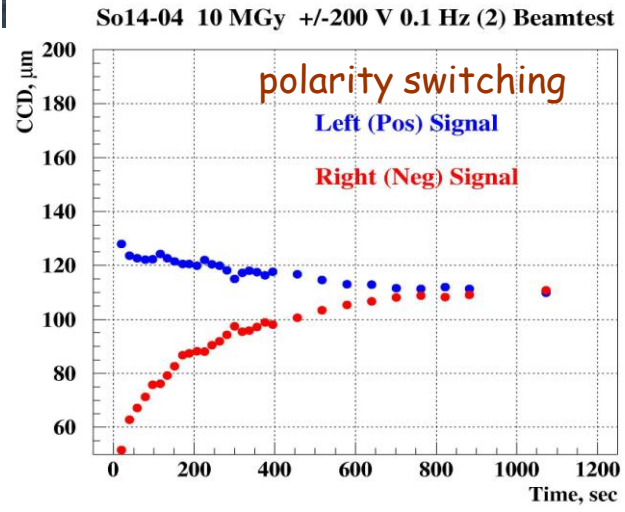
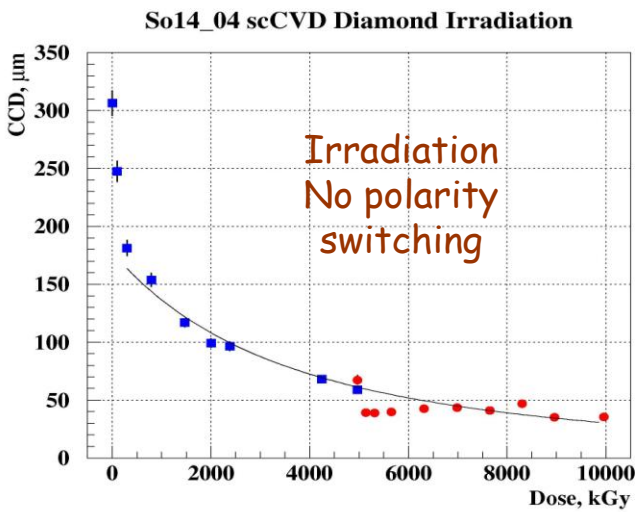
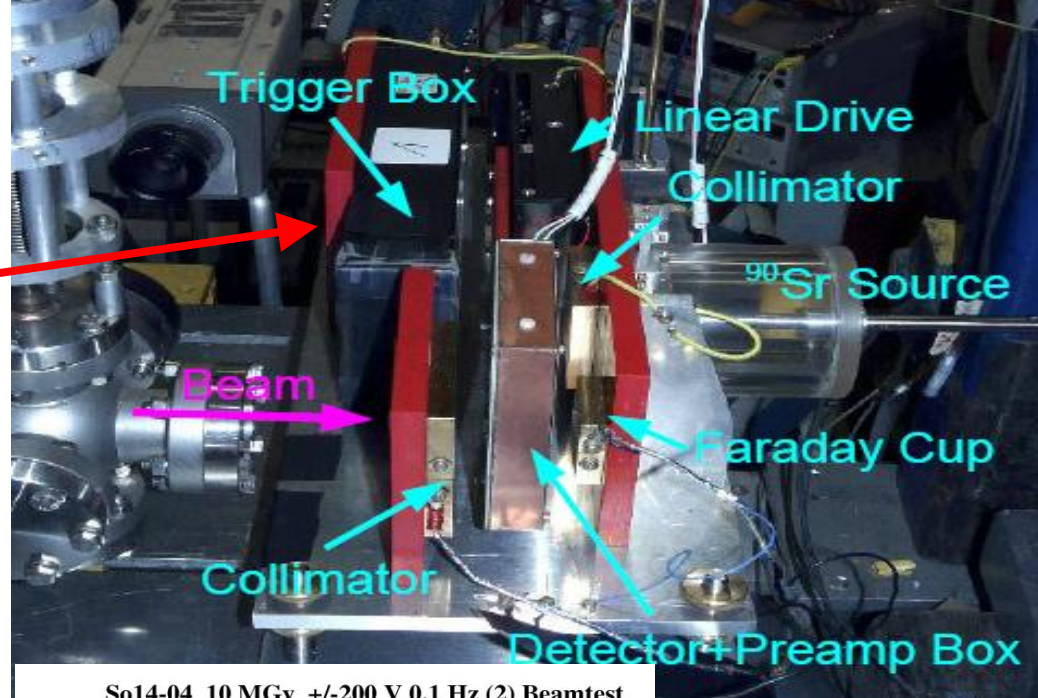
# Infrastructure: High dose irradiation at the beam



# Infrastructure: BeamCal Sensors study at the beam

## Setup for Beam Pumping Measurements

scCVD diamond (E6), 5x5x0.3 mm<sup>3</sup>  
 Irradiated in 2007 up to 5 MGy  
 2008: up to 10 MGy



Infrastructure summary: EUDET-Report-2009-08 VFCAL task status report

# Sensor prototypes (LumiCal, deliverable)

EUDET-Memo-2009-07 J.Blocki, W.Daniluk, E.Kielar et al.,  
Silicon Sensors Prototype for LumiCal Calorimeter



## "Cracow-Design"

- High resistivity n-type Si
- 1,7mm p<sup>+</sup> - strips with an Al-metallization
- Backplane: n<sup>+</sup> implant and an Al-metallization
- 3 Guard rings

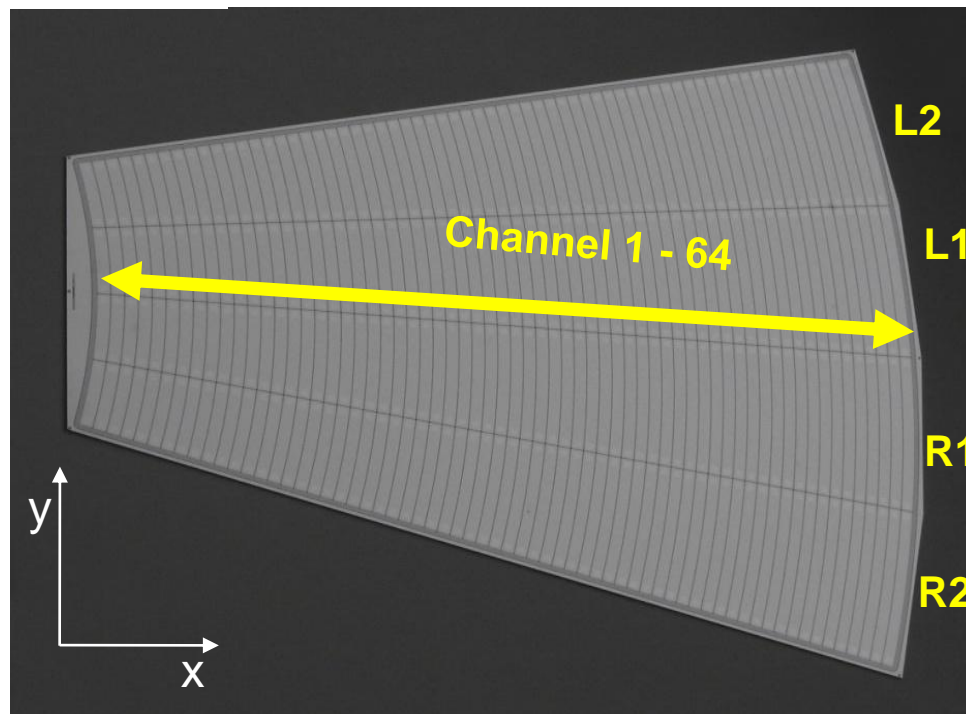
x-Size = 10,8cm

y-Size = 4...12cm

(6 Inch Wafers)

**40 sensors produced by  
Hamamatsu Photonics**

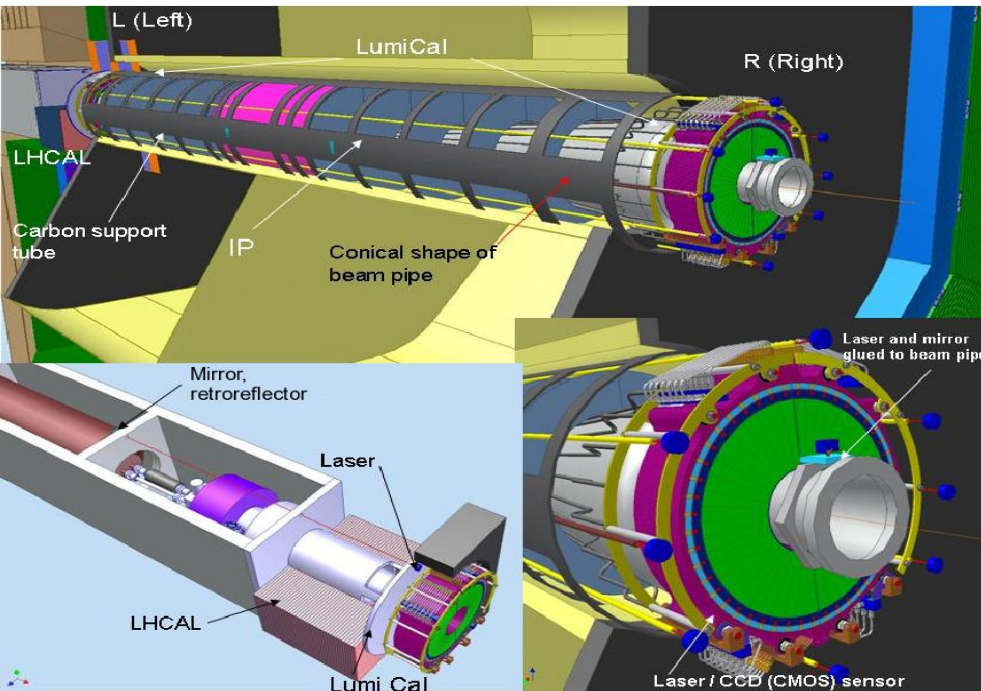
Hamamatsu  
S10938-8380



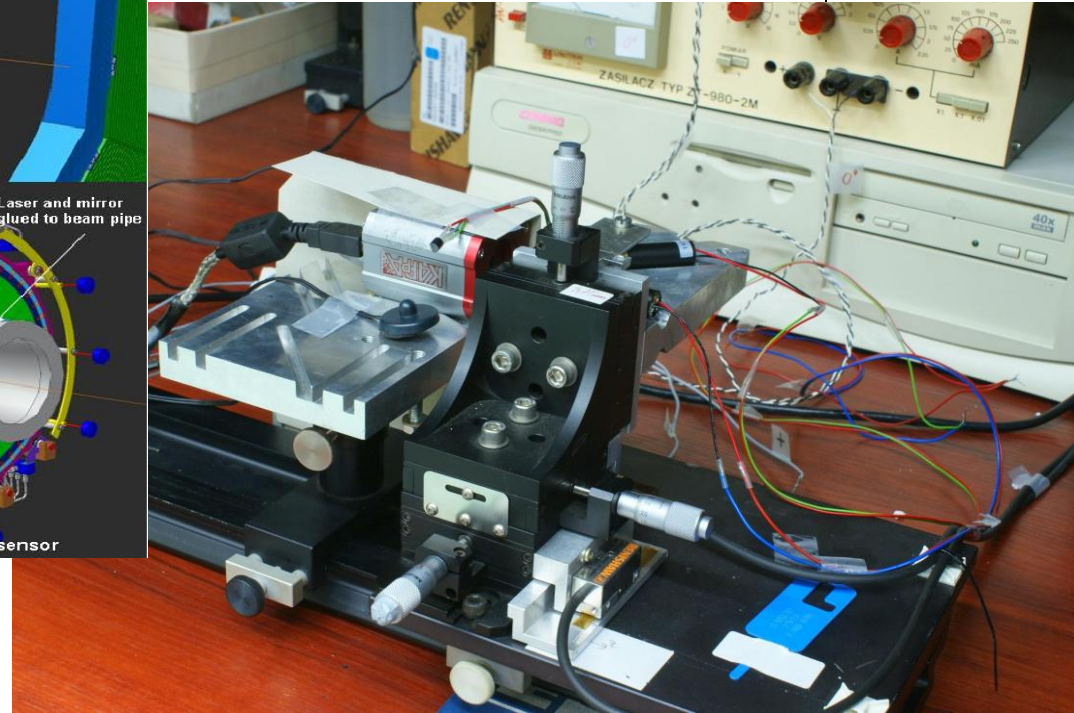
I(V) and C(V) measurements on Probestations in Tel Aviv, Cracow and DESY



# Laser Alignment system (LumiCal)



LAS prototype



**EUDET-Report-2008-05**

**W.Daniluk et al., Laser Alignment System for LumiCal.**

**EUDET-Report-2009-08**

**VFCAL task status report, S.Schuwalow for FCAL Collaboration**

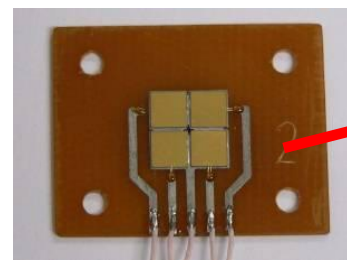
# BeamCal Sensors example

## Baseline: GaAs

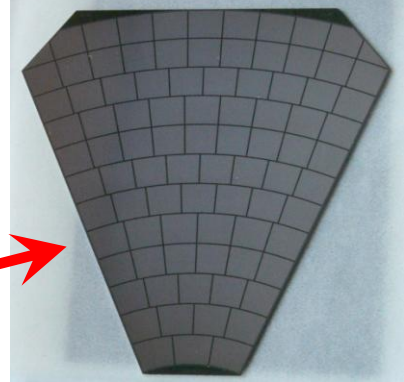
Up to 600 kGy a MIP signal from all sensors is clearly seen

Sensors with a lower concentration of shallow donor and Cr as deep acceptor show better radiation tolerance (up to 1 MGy)

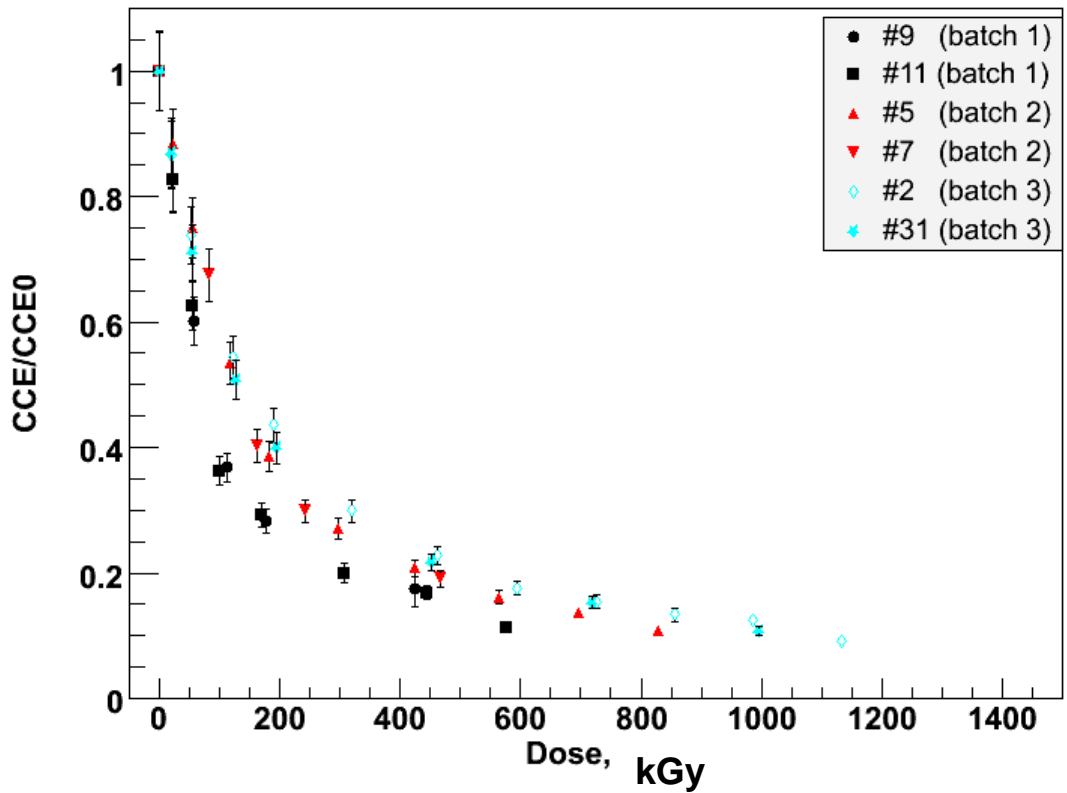
GaAs



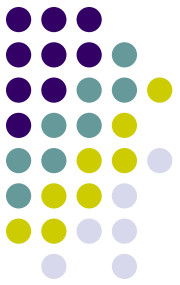
GaAs:Cr CCE vs dose



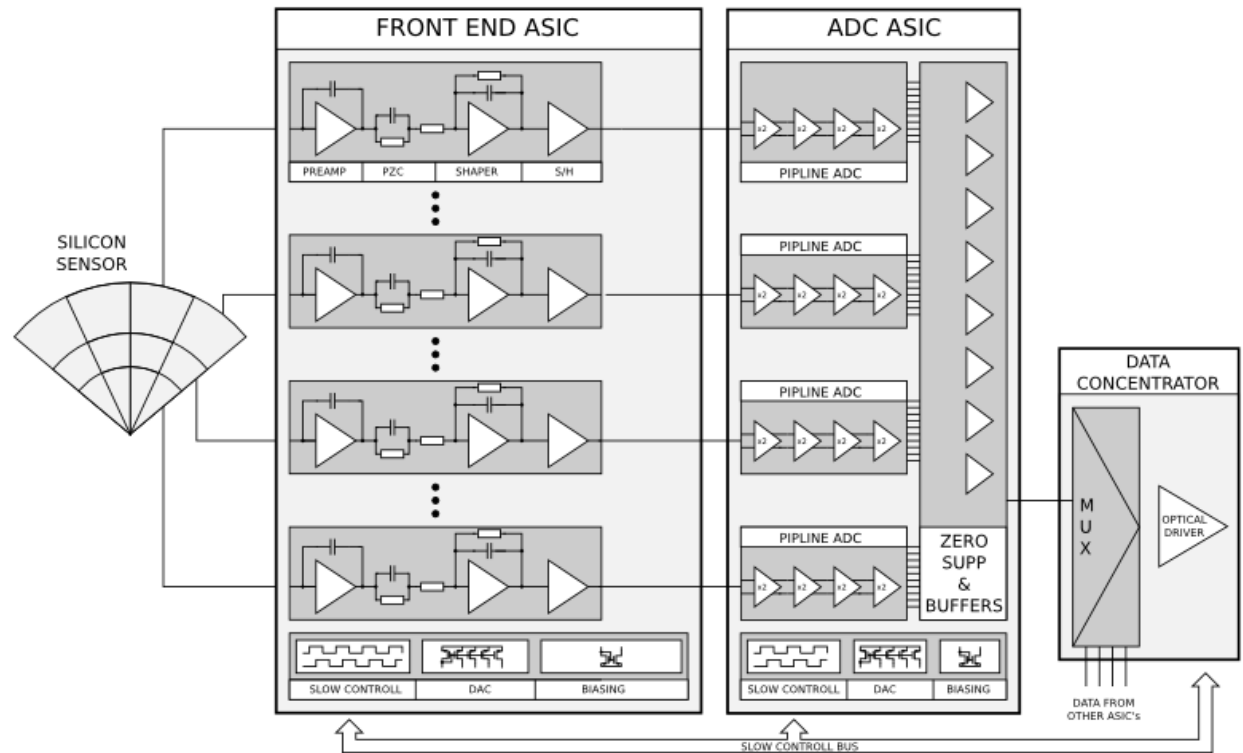
BeamCal sector prototype



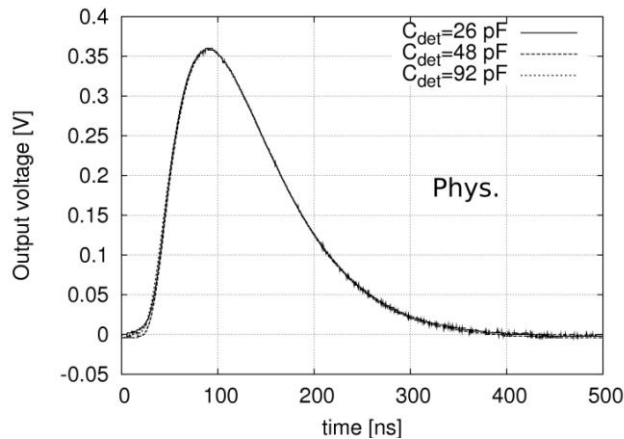
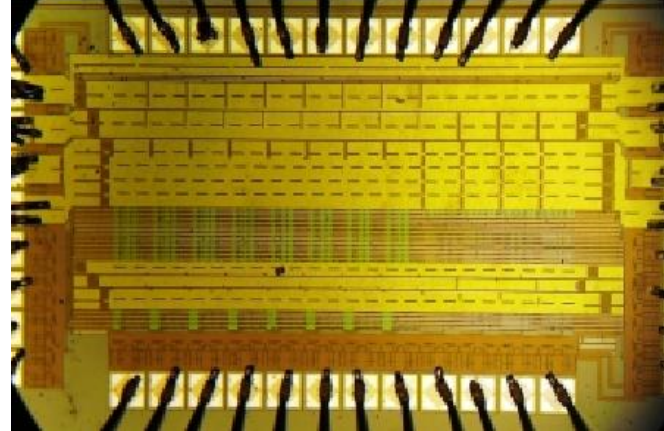
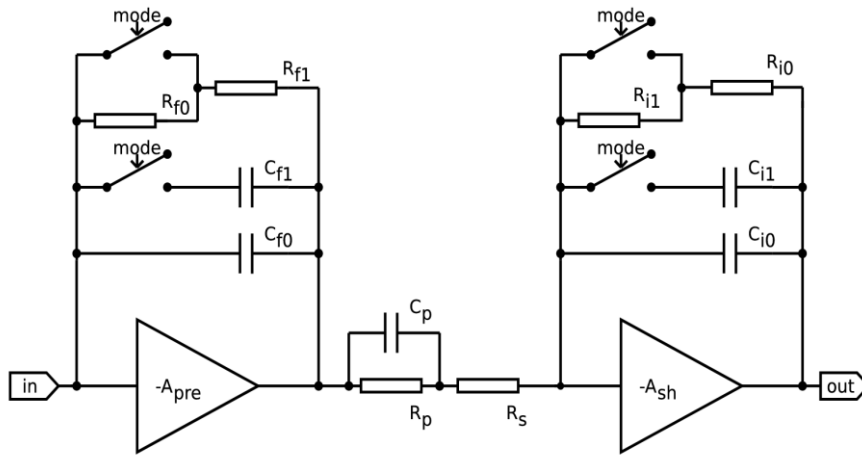
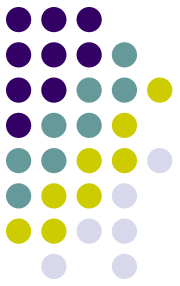
# Readout architecture for luminosity detector at ILC



- Prototypes in AMS 0.35  $\mu\text{m}$ 
  - 8 channels front-end (already presented)
  - 1 channel ADC (measurements completed recently)
  - 8 channels ADC (measurements just started)

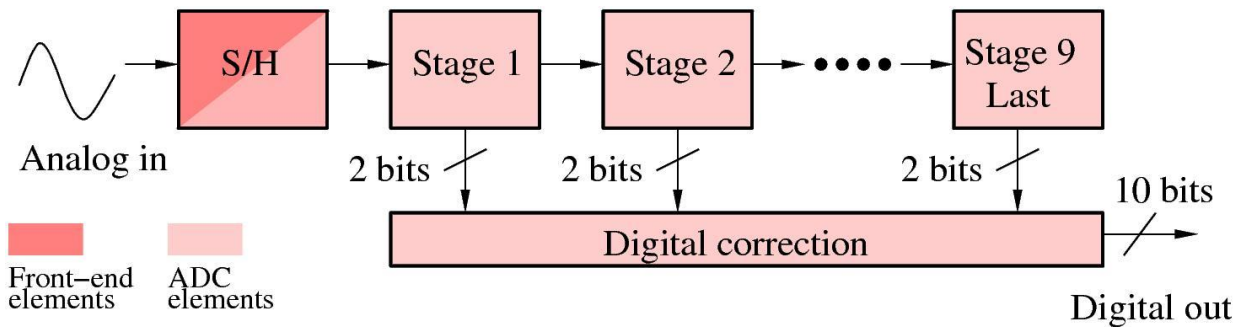


# Preamplifier & PZC & Shaper

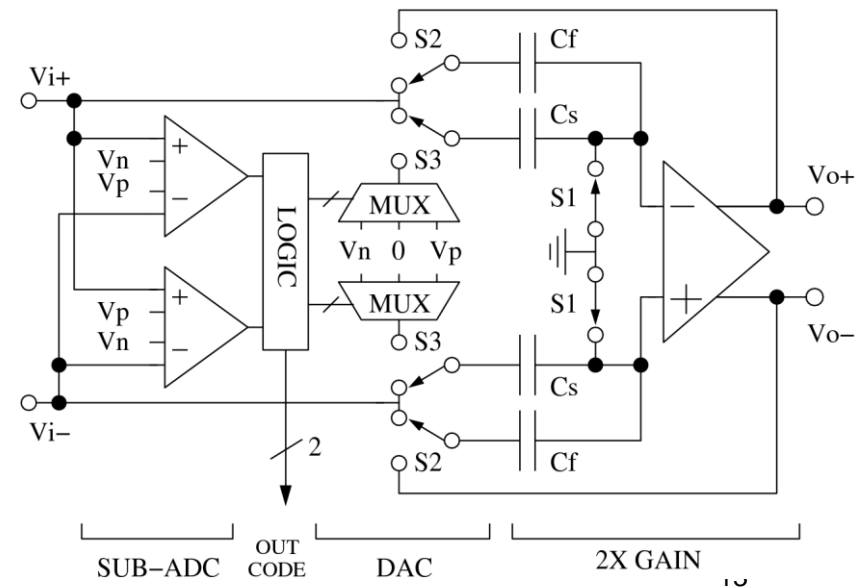


- ❑ ASIC with 8 channels
- ❑ Variable gain (MIPs and high input charge up to  $\sim 10\text{pC}$ )
- ❑  $C_{\text{det}}$  range  $\sim 0\text{-}500\text{ pF}$
- ❑ 1<sup>st</sup> order shaper  $T_{\text{peak}} \sim 60\text{ ns}$
- ❑ Power consumption  $< 9\text{ mW/chan}$

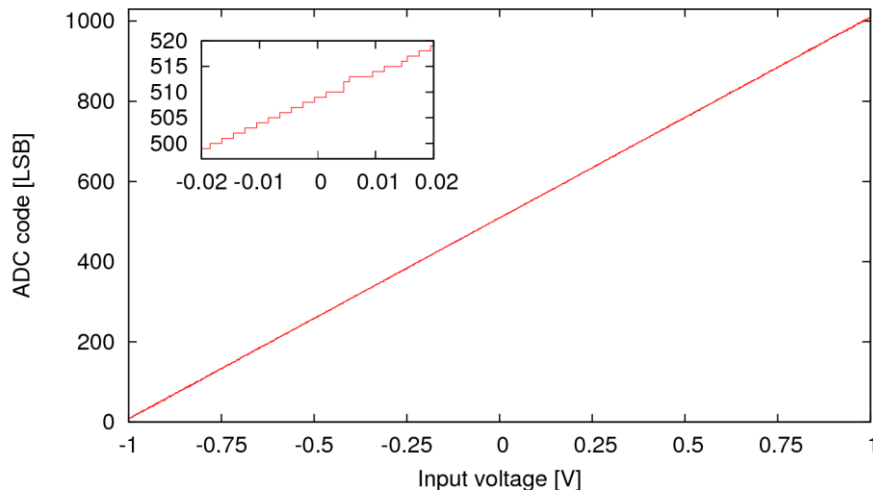
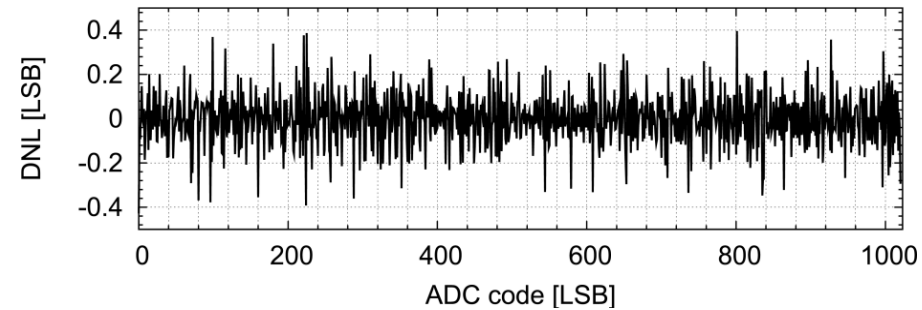
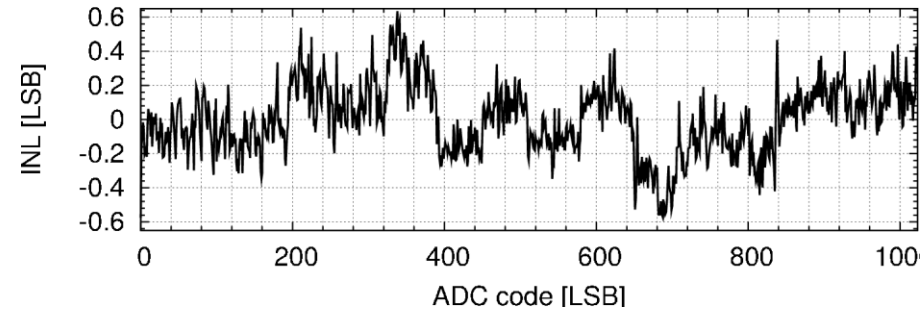
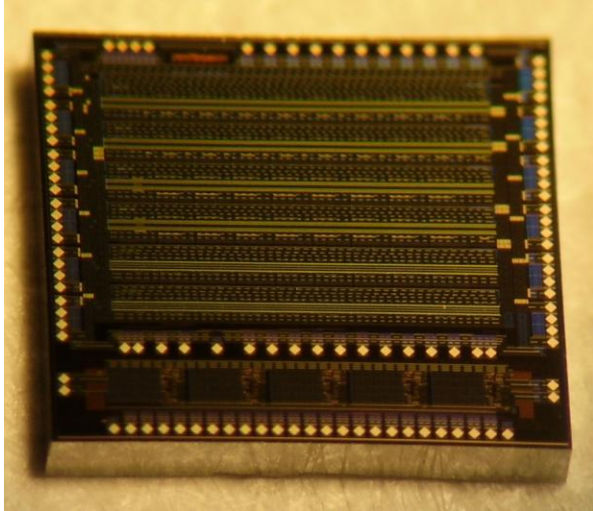
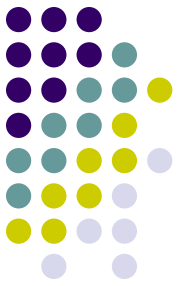
# Design of 10 bit pipeline ADC



- ❑ 10 bit pipeline ADC 1.5 bit/stage
- ❑ Variable sampling frequency up to ~25 Ms/s
- ❑ Scalable power consumption
- ❑ Fully differential
- ❑ Power switching OFF/ON (ILC, CLIC beam timing)
- ❑ Present version in 0.35  $\mu\text{m}$  AMS

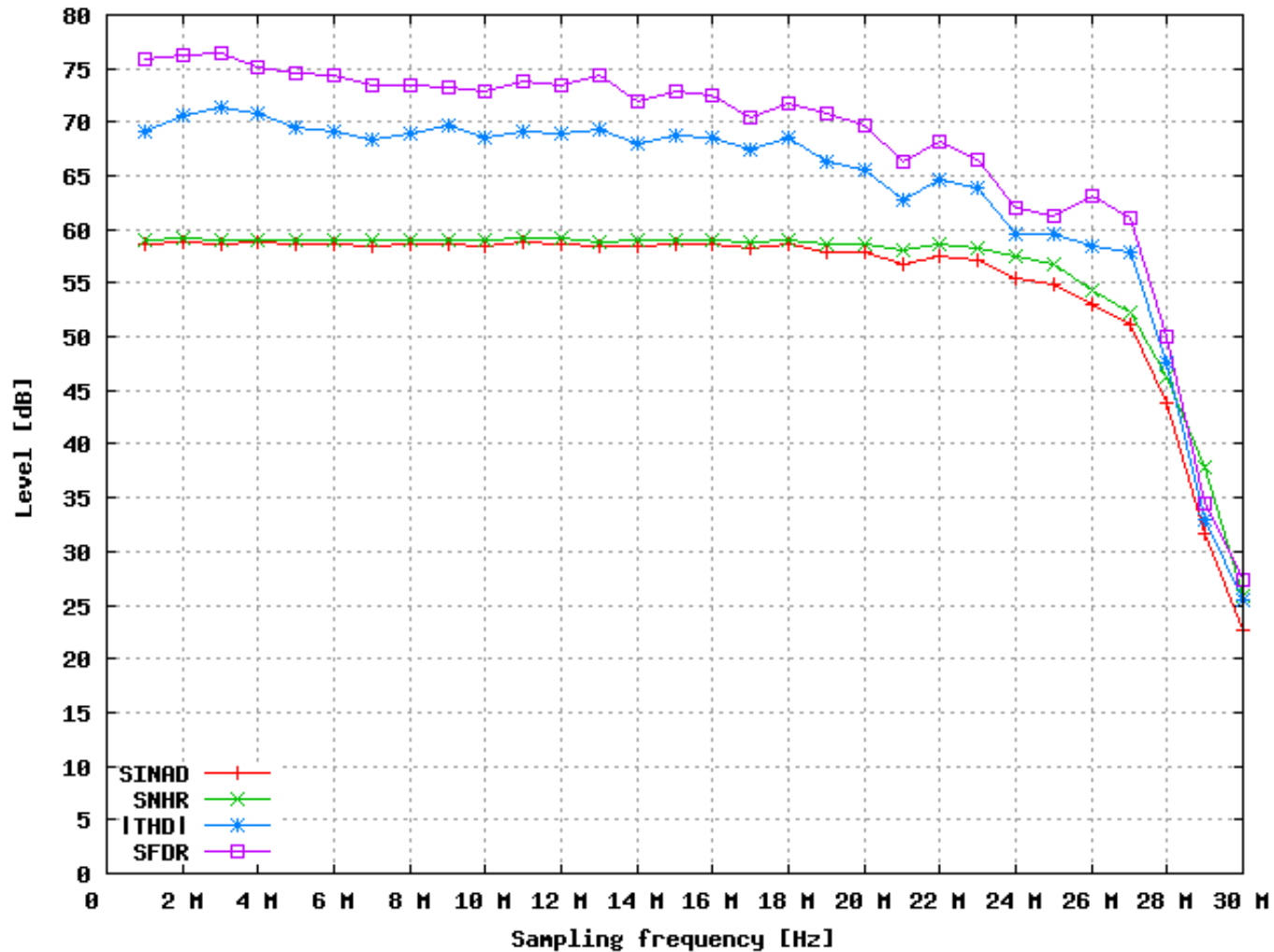
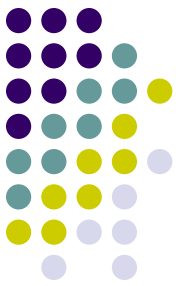


# ADC static measurements



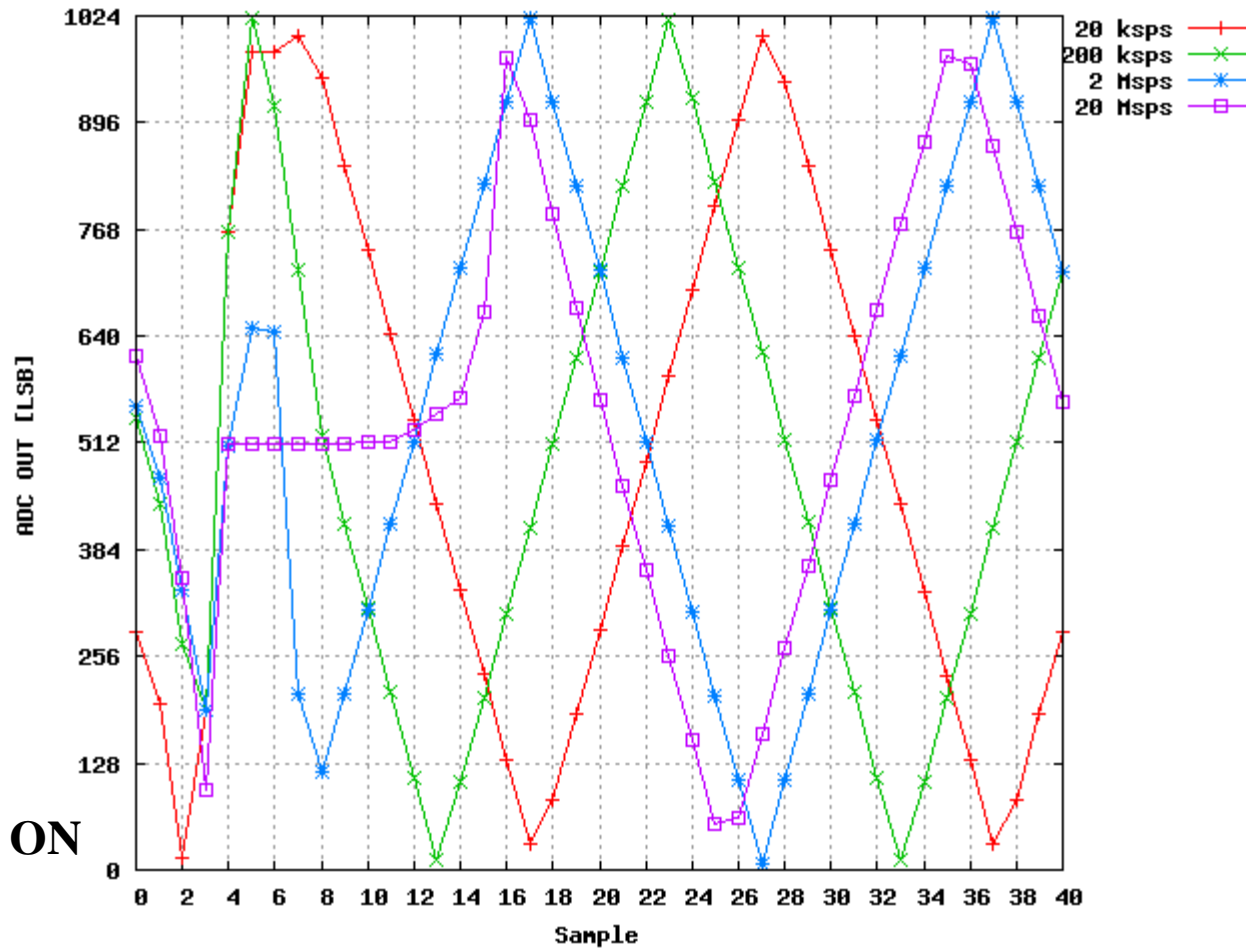
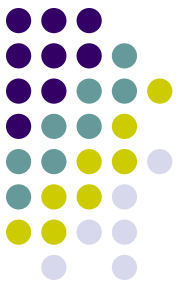
Very good linearity  
 $INL < 1LSB$ ,  $DNL < 0.5 LSB$

# ADC dynamic measurements



Good dynamic performance ENOB ~ 9.5 bit

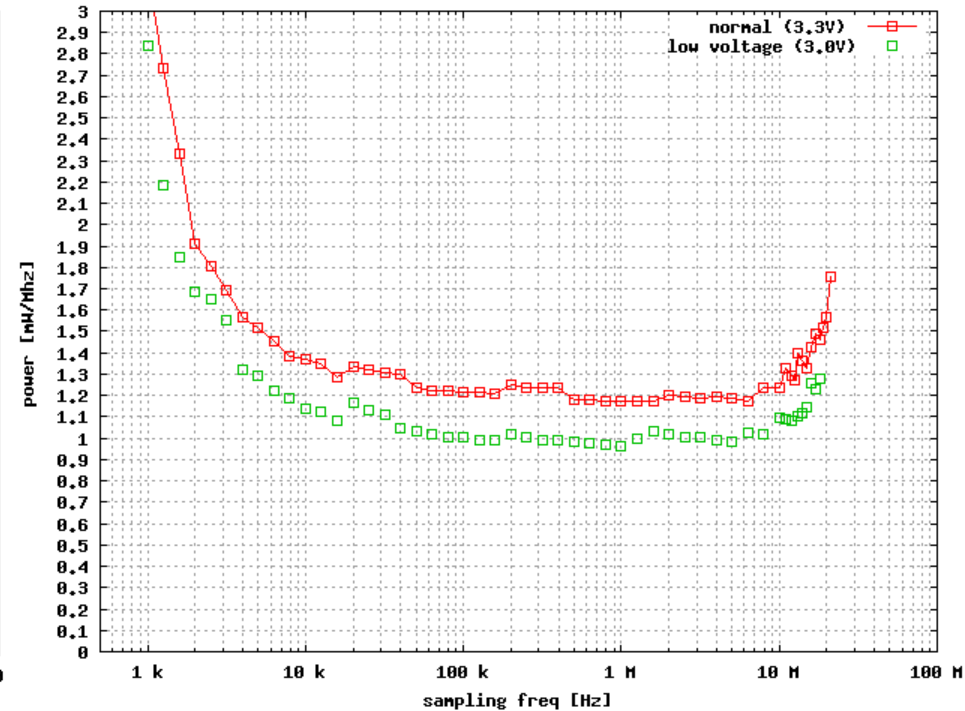
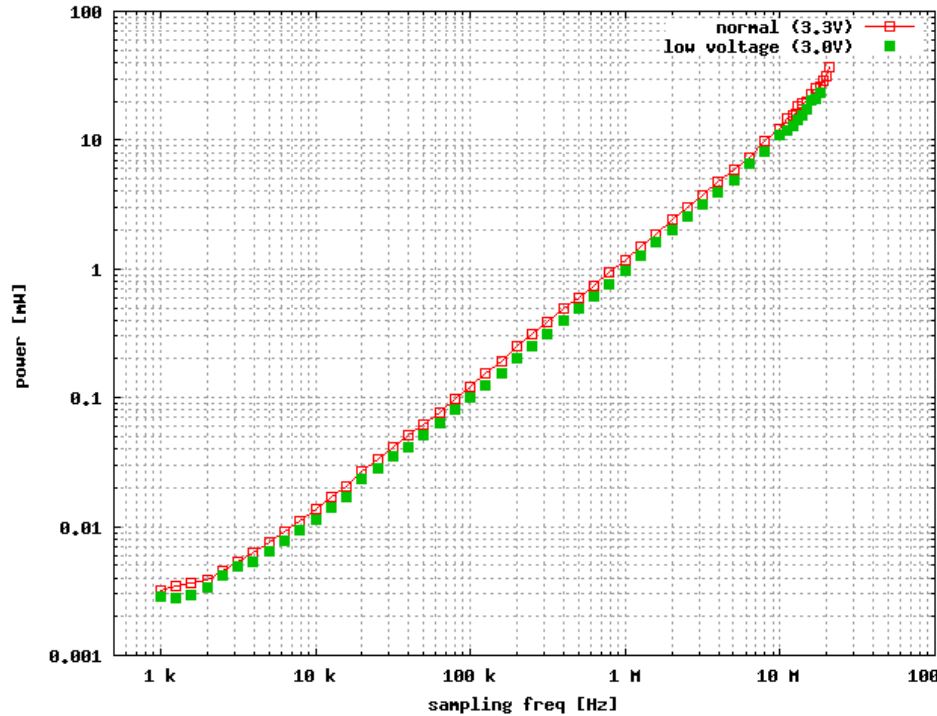
# ADC – power OFF/ON



Depending on sampling frequency 8-16 clocks needed for switching ON



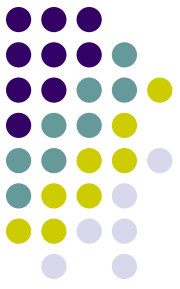
# ADC power consumption



Presently power consumption about 1 mW/MHz (Nyquist input frequency, including output buffers)

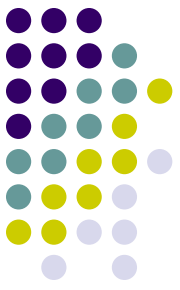
The tests confirmed that ADC fulfils all specifications and may be used in multichannel readout

# Multichannel ADC

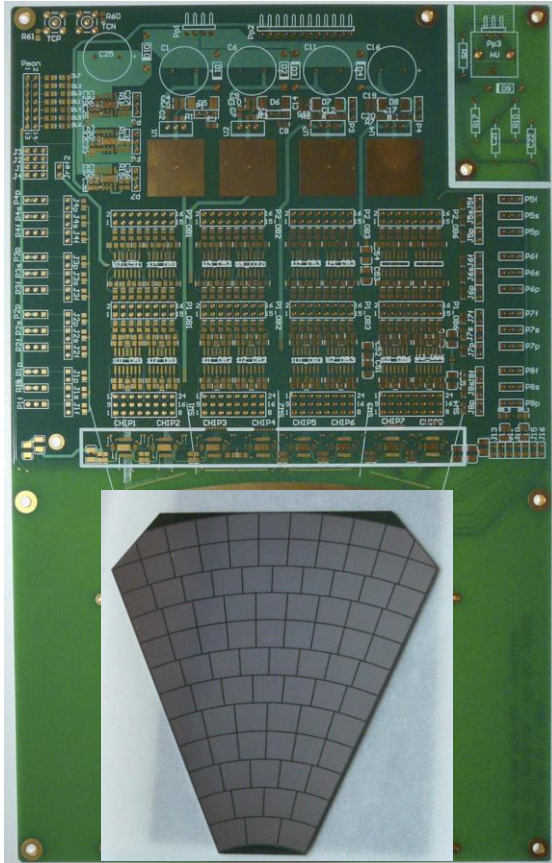


- An 8 channels ADC with 200um pitch was designed and the prototypes were produced recently
- In addition to previous design (containing: power ON/OFF, temperature sensor, fast LVDS – tested to > 800MHz) the ASIC contains DACs allowing automatic power scaling
- The measurements have been just started and quantitative results will be available soon...
- The first measurements show that all 8 channels are working properly and the overall performance seem to be similar to single channel version or slightly better

# System Test (Sensors, Fanout, FE electronics)



(Last year slide)



Template of a readout board, to be instrumented with FE ASICs

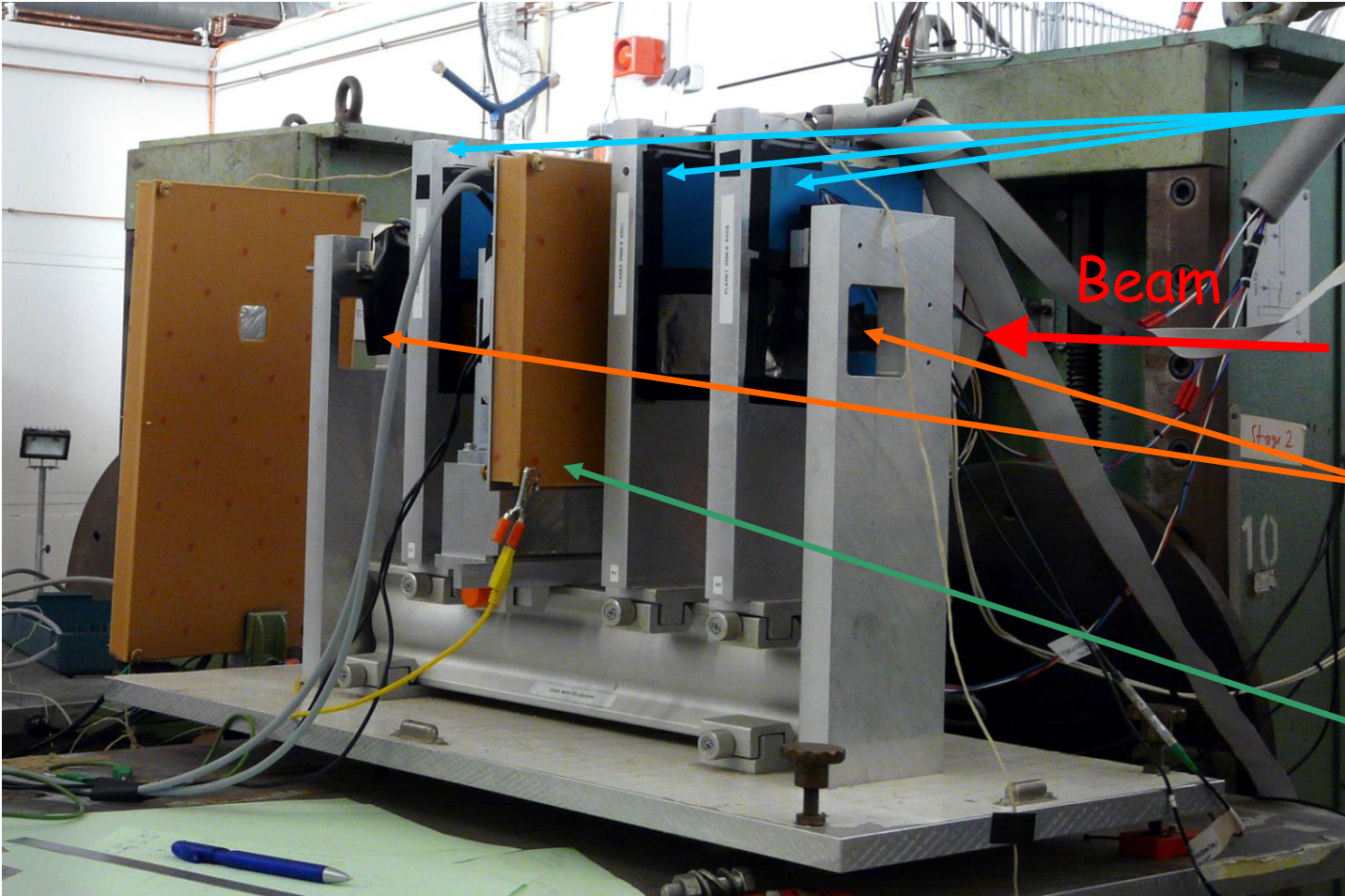
## Readout/Fanout of sensors

- state of the art fine pitch PCB, (100...200 $\mu$ m for current few channel FE chips)
- matters of crosstalk & capacitive load
- wire bonding or bump bonding to pads (wire bonding needs  $\sim$  3mm gap between absorber tiles; conductive glueing also discussed)
- wire bonding to FE chip
- Silicon and GaAs sensor samples
- Beam test planned 2010

# System tests: testbeam @ DESY, August 2010



4.5 GeV electron beam



ZEUS telescope

Beam

Trigger counters

Detector box



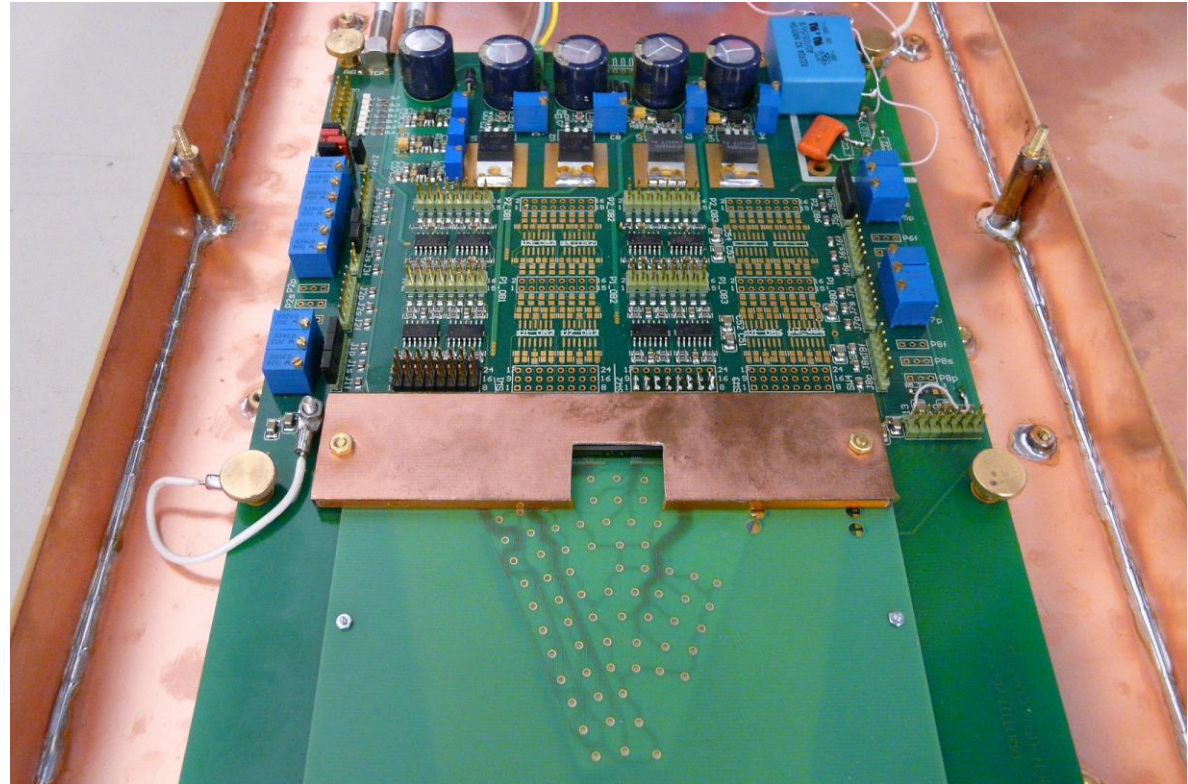
# System tests: testbeam @ DESY, August 2010

Precise XY-table



31 August 2010

Detector box (BeamCal sensor installed)



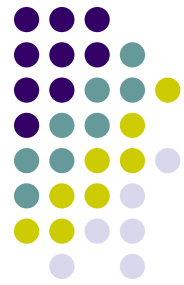
Similar box for the LumiCal sensor

EUDET extended steering committee, DESY

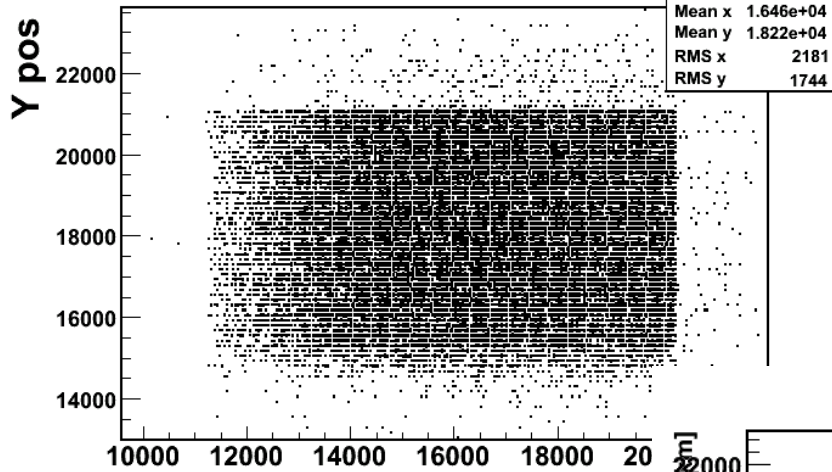
21

# System test: testbeam @ DESY, August 2010

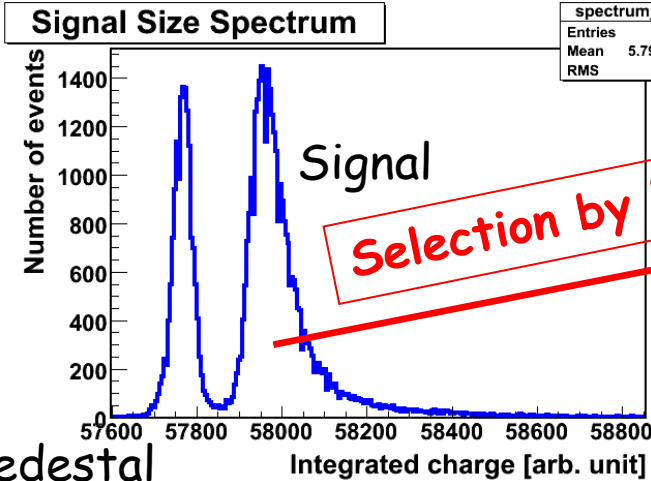
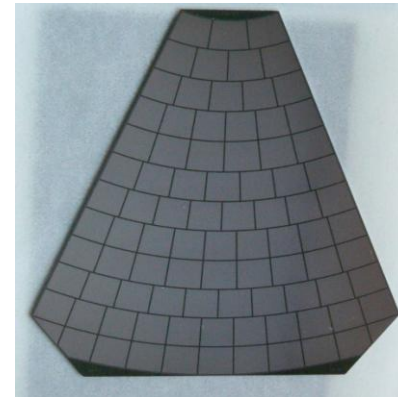
## First results for BeamCal sensor prototype



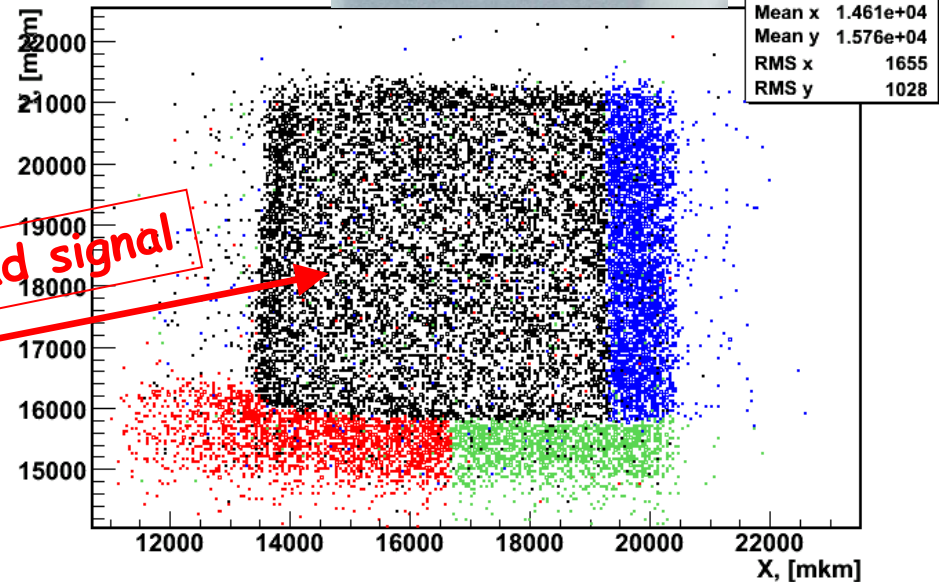
Beam XY profile (mkm)



GaAs sensor



**Selection by Pad signal**



# Next: System test in a beam with FCAL module -> FP7

Infrastructure to verify performance simulations:

A flexible tungsten absorber structure, depth  $10 X_0$ , precise mechanics

Multichannel FE and ADC ASICS to instrument 10 consecutive sensor layers

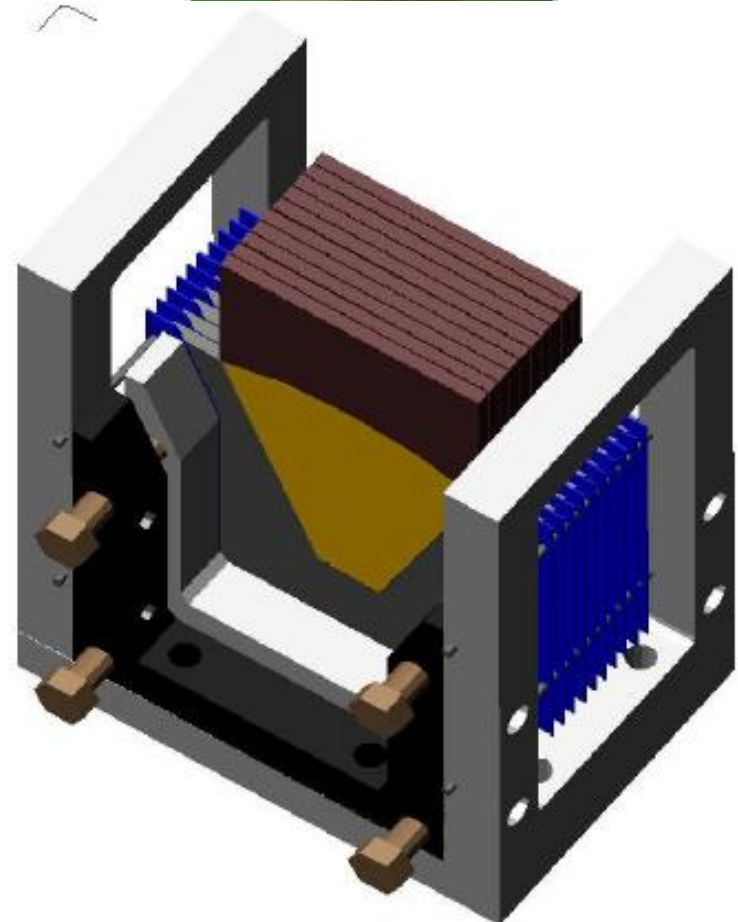
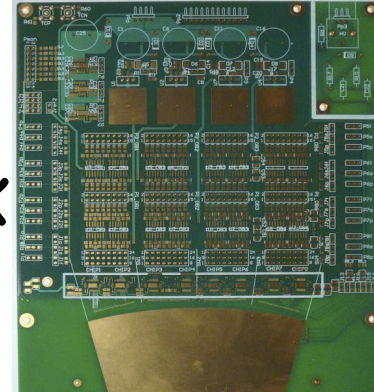
Tools to assembly 10 sensor sectors

Optical position control of the sensor sectors wrt the tungsten frame

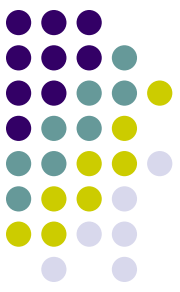
DAQ (common with other components)

Power pulsing (common developments)

10x



# Conclusions



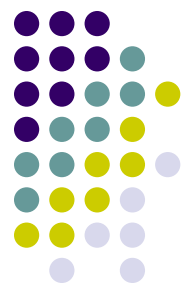
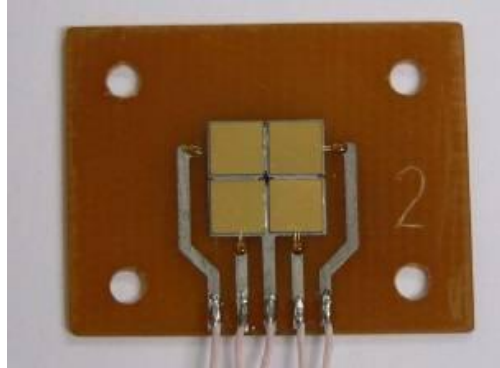
- Infrastructure for VFCAL sensors evaluation is ready
- Prototyping of Si sensors for LumiCal successful. Sensors are tested using probe stations at Cracow, DESY and Tel-Aviv
- Laser Alignment System prototype completed
- FE ASICS are ready and tested with sensors
- System test (sensors+fanout+FE) at DESY testbeam done
- ADC ASICs - second submission successful, first prototypes of multichannel version are under test
- Investigation of the radiation hardness of GaAs, Diamond and Sapphire BeamCal sensor prototypes done up to 12 MGy dose
- NEXT: FCAL Module system test at the beam in future (FP7)



# Backup slides



# BeamCal Sensors, GaAs



- n-type (Te or Sn - shallow donor) GaAs grown by Liquid Encapsulated Czochralski (LEC) method in Siberian Institute of Physics and Technology (Tomsk, Russia)
- low-ohmic material, filling the electron trapping centers EL2+
- Cr (deep acceptor) diffusion -> high-ohmic

Thicknesses 150 - 200  $\mu\text{m}$

Metallization:  
V (30 nm) + Au (1  $\mu\text{m}$ ) from both sides

Irradiation in a 8,5 MeV electron Beam, Doses up to 1.5 MGy

Initial n-GaAs	Fabrication method
№1, $n \approx (1 - 1.5) \cdot 10^{17} \text{ cm}^{-3}$ , Te	Diffusion of Cr under temperature T2
№2, $n \approx (5 - 6) \cdot 10^{16} \text{ cm}^{-3}$ , Te	Diffusion of Cr under temperature Tm
№3, $n \approx (1 - 3) \cdot 10^{16} \text{ cm}^{-3}$ , Sn	Diffusion of Cr under temperature T1
№4, $n \approx (2 - 5) \cdot 10^{16} \text{ cm}^{-3}$ , Te	p-v-n- structure*

Notice  $T1 < Tm < T2$ .

\* - presence in the detector n- type low-resistance domain, all other detectors №1, 2, 3 had structure m-i-m: metal- insulator (high-resistance GaAs) –metal.

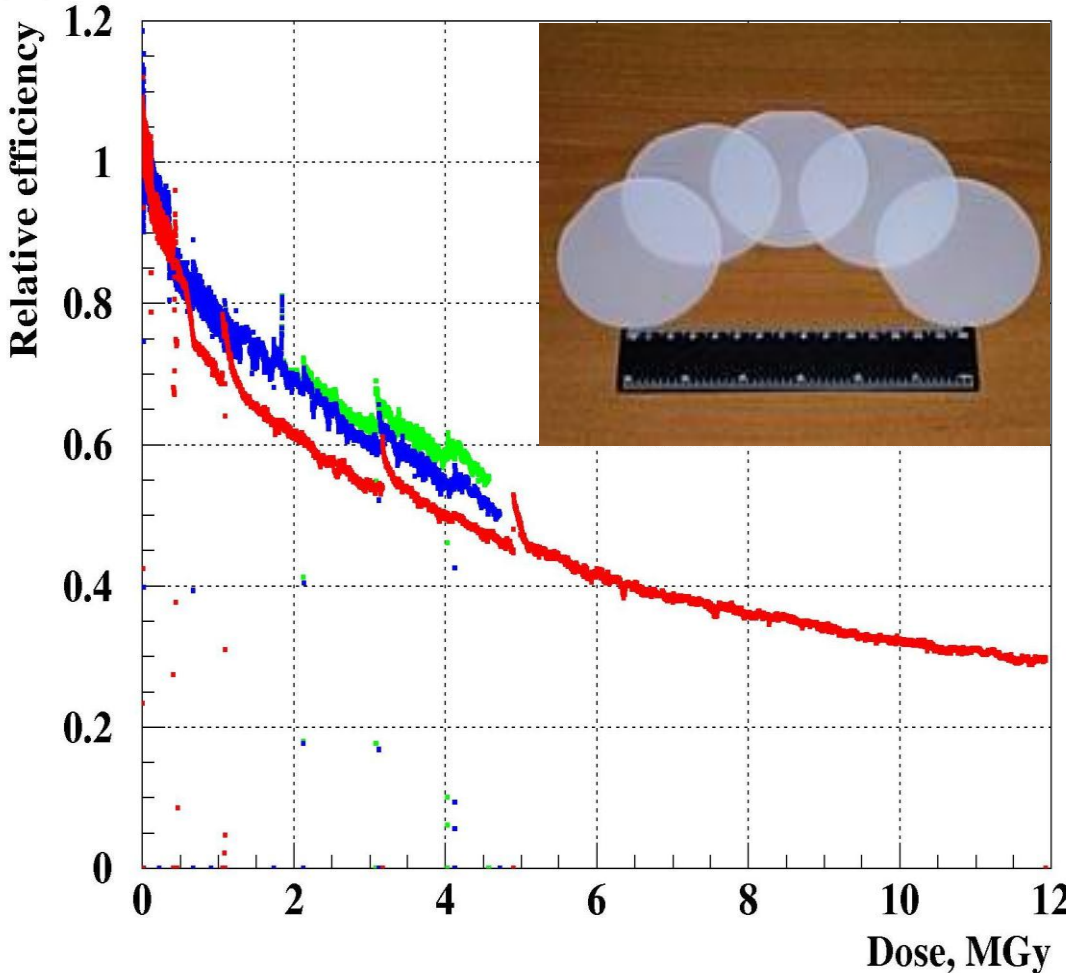
# BeamCal Sensors, Sapphire

Sapphire Crb2 and Crb6 samples

Band gap: 9.9 eV  
(diamond: 5.5 eV, Si: 1.12 eV)  
Single crystal, 1x1x0.05 cm<sup>3</sup>  
Wafer: up to 30 cm diameter  
Metallization: Al 200 nm or  
50/50/100 nm Al/Ti/Au



Normalized ratio of the detector and Faraday cup currents

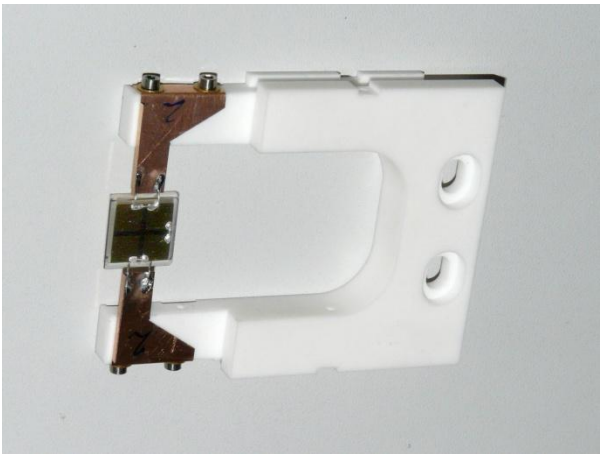


Charge collection efficiency: few % for nonirradiated samples  
~ 30 % of the initial charge collection efficiency after 12 MGy

# Test in PITZ

Electron beam, 14.5 MeV, bunches

Diamond sensor was installed in the vacuum of the beam pipe



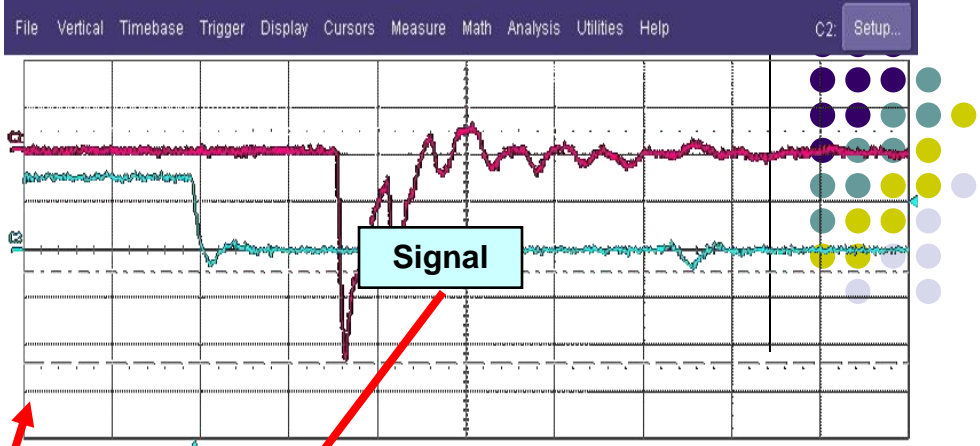
Moving the sensor through an electron beam,

Bunch charge 1 pC - 1 nC,

Beam spot: few mm<sup>2</sup>

Beam profile

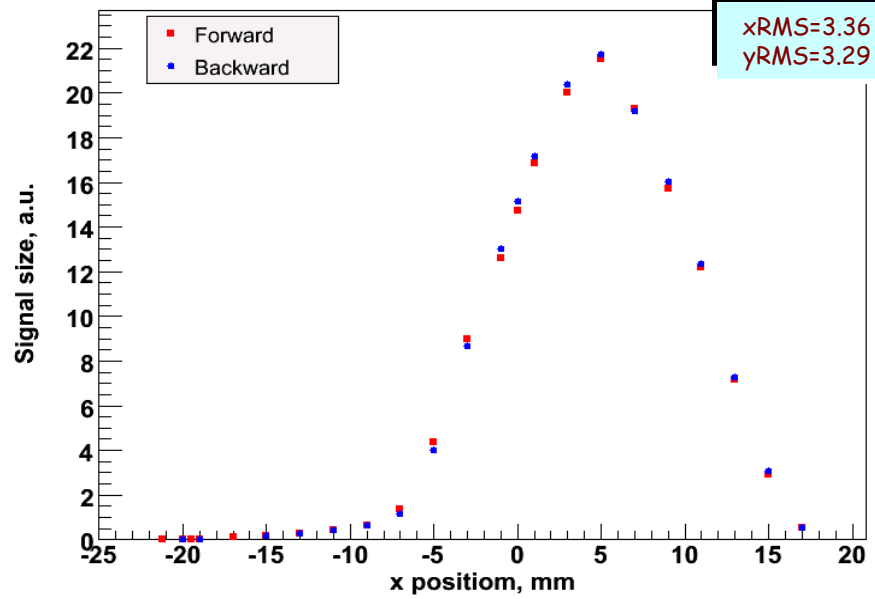
EMI doesn't disturb operation



Bunch train trigger

Channel	Scale	Offset
C2	200 mV/div	420.0 mV
C3	2.00 V/div	0 mV offset

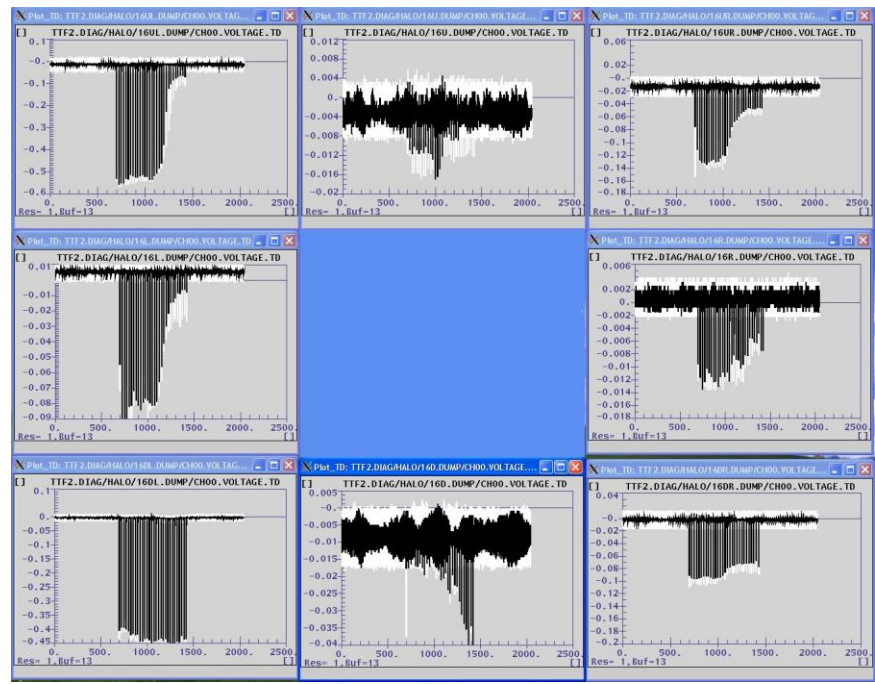
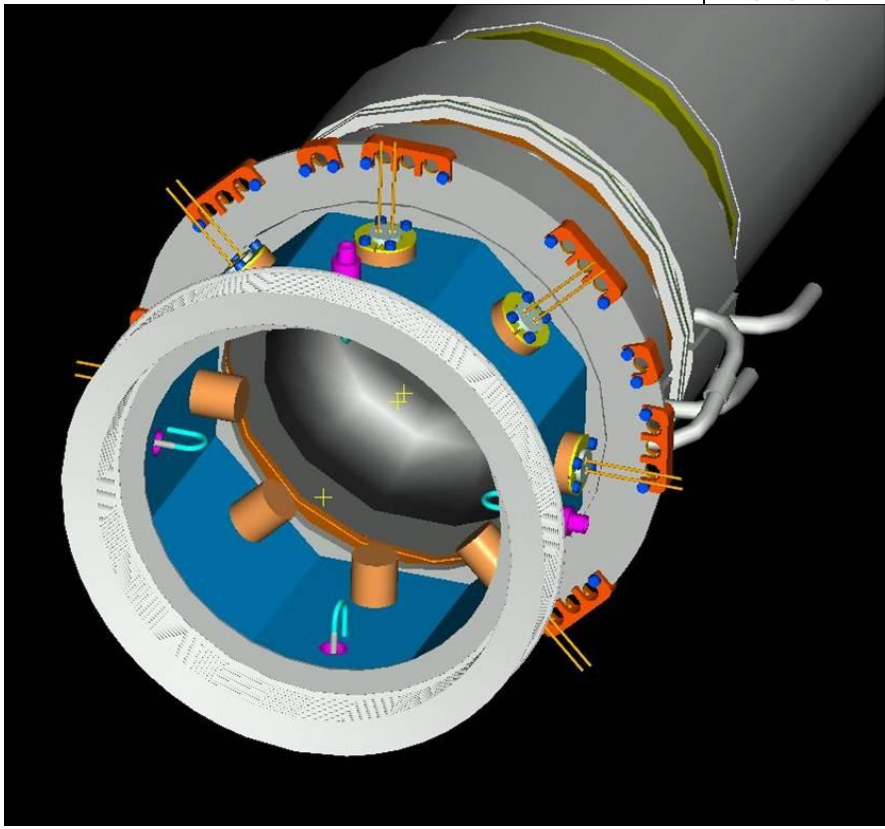
E6\_B2 signal size vs x position (200 V, 10 pC, unfocused)



# Application at FLASH

FCAL designed, constructed and installed a Beam-Condition Monitor at FLASH (4 diamond and 4 sapphire sensors)

Operation in the "9 mA" run of FLASH was successful



# Design of 10 ADC...



- The second ADC version contains:
  - 9 pipeline stages plus S/H stage
  - Power ON/OFF feature
  - Bandgap based precise voltage reference plus temperature sensor
  - LVDS transmitter and receiver I/O circuits simulated up to about 1 GHz